

The documentation and process conversion measures necessary to comply with this document shall be completed by 12 December 2003.

INCH-POUND

MIL-PRF-19500/567C  
 12 September 2003  
 SUPERSEDING  
 MIL-PRF-19500/567B  
 20 July 2001

PERFORMANCE SPECIFICATION

\* SEMICONDUCTOR DEVICE, DIODE, SILICON,  
 SCHOTTKY BARRIER, FAST RECOVERY,  
 TYPE 1N6492, 1N6492U4, JAN, JANTX, JANTXV, AND JANS

This specification is approved for use by all Departments  
 and Agencies of the Department of Defense.

1. SCOPE

1.1 Scope. This specification covers the performance requirements for silicon, fast recovery, Schottky barrier, semiconductor diode. Four levels of product assurance are provided for each device type as specified in MIL-PRF-19500.

\* 1.2 Physical dimensions. See figure 1 (similar to TO-205AF), and figure 2 (U4).

\* 1.3 Maximum ratings. (1)

Type	V <sub>RRM</sub> and V <sub>RWM</sub> (2)	V <sub>RSM</sub>	V <sub>R</sub> (2)	I <sub>F</sub> 1 (AV) (3) T <sub>A</sub> = +25°C (3)	I <sub>F</sub> 1 (AV) (4) T <sub>C</sub> = +100°C	I <sub>O</sub> T <sub>C</sub> = +100°C (5)	I <sub>FSM</sub>	T <sub>J</sub> and T <sub>STG</sub>
	<u>V (pk)</u>	<u>V (pk)</u>	<u>V dc</u>	<u>A dc</u>	<u>A dc</u>	<u>A dc</u>	<u>A (pk)</u>	<u>°C</u>
1N6492	45	54	45	1.20	4	3.60	80	-65 to +175
1N6492U4	45	54	45	1.20	4	3.60	80	

(1) For thermal impedance see figure 3.

(2) Full rated V<sub>RRM</sub> and V<sub>RWN</sub> with appropriate average forward current (see note (3)) is applicable over the range of T<sub>C</sub> from -55°C to +135°C. Full rated V<sub>R</sub> is applicable over the range of T<sub>C</sub> from -55°C to +120°C. With these maximum voltages and case temperatures, T<sub>J</sub> ≤ +175°C.

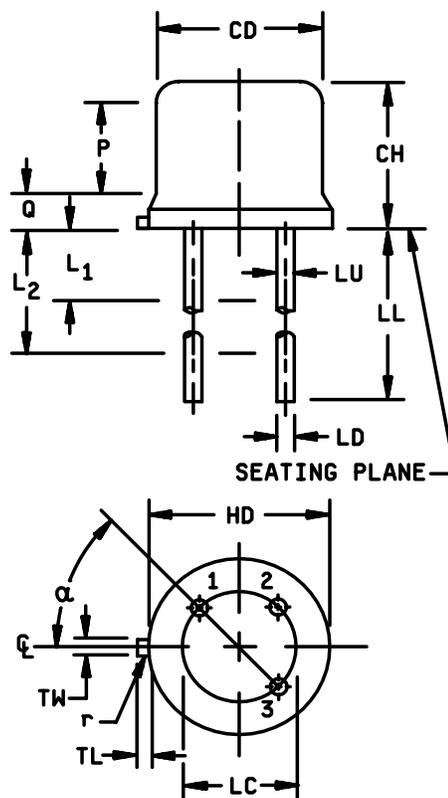
(3) This rating requires no special mounting, heat sinking, or forced air flow across the device.

(4) Average current with a 50 percent duty cycle square wave including reverse voltage amplitude equal to the magnitude of full rated V<sub>RWM</sub>. Derate linearly at 114 mA dc/°C for T<sub>C</sub> > +100°C (to 0 at T<sub>C</sub> = +135°C); if V<sub>RWM</sub> = 20, derate I<sub>F</sub> (AV) at 62 mA/°C, to 0 at T<sub>C</sub> = +165°C.

(5) Average current with an applied sine wave including reverse voltage equal to the magnitude of full rated V<sub>RWM</sub>. Derate linearly at 103 mA dc/°C for T<sub>C</sub> > +100°C; if V<sub>RWN</sub> = 20, derate at 55 mA/°C.

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Defense Supply Center, Columbus, ATTN: DSCC-VAC, P.O. Box 3990, Columbus, OH 43216-5000, by using the Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.

Ltr	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
CD	.305	.335	7.75	8.51	
CH	.160	.180	4.07	4.57	
HD	.335	.370	8.51	9.40	
LL	.500	.750	12.7	19.05	8, 9
LC	.200 TP		5.08 TP		7
LD	.016	.021	0.41	0.53	8, 9
LU	.016	.019	0.41	0.48	8, 9
L1		.050		1.27	8, 9
L2	.250		6.35		8, 9
P	.100		2.54		6
Q		.040		1.02	5
r		.010		0.018	10
TL	.029	.045	0.74	1.14	
TW	.028	.034	0.72	0.86	
$\alpha$	45° TP		45° TP		7
Term 1	Anode				
Term 2	Open (no connection)				
Term 3	Cathode (case)				

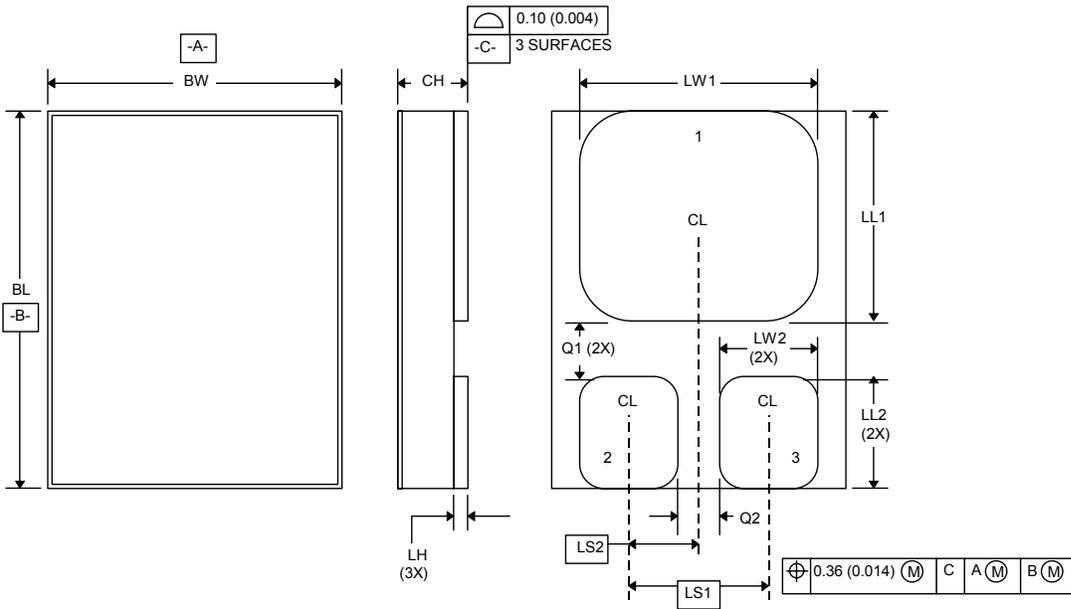


NOTES:

1. Dimensions are in inches.
2. Metric equivalents are given for general information only.
3. Beyond radius (r) maximum, TW shall be held for a minimum length of .011 inch (0.028 mm).
4. Dimension TL measured from maximum HD.
5. Outline in this zone is not controlled.
6. Dimension CD shall not vary more than .010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
7. Leads at gauge plane .054 +.001, -.000 inch (1.37 +0.03, -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. The device may be measured by direct methods.
8. LU applies between L<sub>1</sub> and L<sub>2</sub>. LD applies between L<sub>2</sub> and LL minimum. Diameter is uncontrolled in L<sub>1</sub> and beyond LL minimum.
9. All three leads.
10. Radius (r) applies to both inside corners of tab.
11. Cathode is electrically connected to the case.
12. In accordance with ASME Y14.5M, diameters are equivalent to  $\phi$ x symbology.

\* FIGURE 1. Physical dimensions (similar to TO-205AF).

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Symbol	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
BL	.215	.225	5.46	5.72
BW	.145	.155	3.68	3.94
CH	.050	.070	1.27	1.77
LH		.020		0.50
LW1	.135	.145	3.43	3.68
LW2	.047	.057	1.19	1.45
LL1	.085	.125	2.16	3.17
LL2	.045	.075	1.14	1.91
LS1	.065	.095	1.65	2.41
LS2	.033	.048	.825	1.21
Q1	.045	.070	1.14	1.78
Q2	.025	.048	.635	1.22
TERM 1	Collector			
TERM 2	Base			
TERM 3	Emitter			

NOTES:

1. Dimensions are in inches.
2. Metric equivalents are given for general information only.

\* FIGURE 2. Physical dimensions and configuration (U4).

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\* 1.4 Primary electrical characteristics at  $T_A = +25^\circ\text{C}$ , unless otherwise indicated.

Type	$V_{FM1}$ $I_{FM} = 4 \text{ A (pk)}$	$V_{FM2}$ $I_{FM} = 2 \text{ A (pk)}$	$I_{RM}$ $V_{RM} = 45 \text{ V (pk)}$ $T_J = +125^\circ\text{C}$	$I_{RM}$ $V_{RM} = 45 \text{ V (pk)}$ $T_J = +25^\circ\text{C}$	$C_T$ $V_R = 5 \text{ V dc}$	$R_{\theta JC}$	$R_{\theta JA}$
	<u>V (pk)</u>	<u>V (pk)</u>	<u>mA (pk)</u>	<u>mA (pk)</u>	<u>pF</u>	<u>°C/W</u>	<u>°C/W</u>
1N6492	0.68	0.56	20	2.0	450	12.0	175
1N6492U4	0.68	0.56	20	2.0	450	12.0	175

2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3 and 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements documents cited in sections 3 and 4 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation (see 6.2).

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-19500 - Semiconductor Devices, General Specification for.

STANDARD

DEPARTMENT OF DEFENSE

MIL-STD-750 - Test Methods for Semiconductor Devices.

(Unless otherwise indicated, copies of the above specifications, standards, and handbooks are available from the Document Automation and Production Services (DAPS), Building 4D (DPM-DODSSP), 700 Robbins Avenue, Philadelphia, PA 19111-5094.)

2.3 Order of precedence. In the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

\* 3.1 General. The individual item requirements shall be as specified in MIL-PRF-19500 and as modified herein.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see 4.2 and 6.3).

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3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500.

\* 3.4 Interface and physical dimensions. Interface and physical dimensions shall be as specified in MIL-PRF-19500, and on figure 1, and figure 2 herein.

3.4.1 Lead finish. Lead finish shall be solderable in accordance with MIL-PRF-19500, MIL-STD-750, and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see 6.2).

3.5 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in 1.3, 1.4, and table I herein.

3.6 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table I herein.

3.7 Marking. Marking shall be in accordance with MIL-PRF-19500.

3.8 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- c. Conformance inspection (see 4.4).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500. Alternate flow is allowed for qualification inspection in accordance with figure 4 of MIL-PRF-19500.

\* 4.3 Screening (JANS, JANTX, AND JANTXV levels only). Screening shall be in accordance with table IV of MIL-PRF-19500, and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see table IV of MIL-PRF-19500)	Measurement	
	JANS level	JANTX and JANTXV levels
3	Test condition F $t_{LOW} = -55^{\circ}C$ and $T_{HIGH} = +175^{\circ}C$	Test condition F $t_{LOW} = -55^{\circ}C$ and $T_{HIGH} = +175^{\circ}C$
9	Reverse energy test (see 4.5.2) $V_{FM2}, I_{R1}$	Not applicable
10	$T_C = +130^{\circ}C$	$T_C = +130^{\circ}C$
11	Reverse energy test (see 4.5.2) $\Delta V_{FM2} \pm 50$ mV of initial value $\Delta I_{R1} \pm 100$ percent or 500 $\mu A$ , whichever is greater.	Reverse energy test (see 4.5.2) $V_{FM2}, I_{R1}$
12	See 4.3.1	See 4.3.1
13	Subgroup 2 of table I herein. Reverse energy test (see 4.5.2) $\Delta V_{FM2} \pm 50$ mV $\Delta I_{RM1} \pm 100$ percent or 500 $\mu A$ , whichever is greater. Scope display evaluation (see 4.5.5)	Subgroup 2 of table I herein. Reverse energy test (see 4.5.2) $\Delta V_{FM2} \pm 50$ mV $\Delta I_{RM1} \pm 100$ percent or 500 $\mu A$ , whichever is greater. Scope display evaluation (see 4.5.5)

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\* 4.3.1 Power burn-in conditions. Power burn-in conditions are as follows (in accordance with method 1038 of MIL-STD-750, condition B):  $T_A = +50^\circ\text{C}$  maximum, any clips or heat sink configuration may be utilized provided that  $I_O$  and  $T_A$  are adjusted to achieve  $T_J = +135^\circ\text{C}$  minimum,  $V_R = 45\text{ V (pk)}$ ,  $I_O = 0.75\text{ A dc}$ ,  $f = 60\text{ Hz}$ .

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500. Alternate flow is allowed for qualification inspection in accordance with figure 4 of MIL-PRF-19500.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with MIL-PRF-19500 and table I herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in tables VIa (JANS) and VIb (JAN, JANTX, and JANTXV) of MIL-PRF-19500 and 4.4.2.1 and 4.4.2.2 herein. Electrical measurements (end-points) shall be in accordance with the applicable inspections of table I, subgroup 2 herein. Delta measurements shall be in accordance with table II herein.

\* 4.4.2.1 Group B inspection, table VIa (JANS) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B3	1051	Temperature cycling, condition F, $T_{\text{LOW}} = -55^\circ\text{C}$ , $T_{\text{HIGH}} = +175^\circ\text{C}$ .
B4	1037	$I_O = 0.75\text{ A}$ , $T_A = +25^\circ\text{C}$ ; $V_{\text{RM}} = 45\text{ V}$ , $t_{\text{on}} = t_{\text{off}} = 3\text{ minutes}$ for a minimum of 2,000 cycles.
B5	1027	$I_F = 3.2\text{ A dc}$ minimum adjust $T_A$ or $I_F$ as required $I_F$ or $T_A$ to achieve a lot $T_J = +275^\circ\text{C}$ .
B6	4081	See 4.5.3, $R_{\theta\text{JC}} \leq 12.0^\circ\text{C/W}$ .

\* 4.4.2.2 Group B inspection, table VIb (JAN, JANTX, and JANTXV of MIL-PRF-19500).

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B2	1051	Temperature cycling, condition C.
B3	1027	$T_A = +25^\circ\text{C}$ , $I_O = 0.75\text{ A}$ , $V_{\text{RM}} = 45\text{ V (pk)}$ .
B3	2037	Condition A, all internal wires must be pulled separately.
B5	4081	See 4.5.3, $R_{\theta\text{JC}} \leq 12.0^\circ\text{C/W}$ .
B6	1032	$T_A = +175^\circ\text{C}$ .

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VII of MIL-PRF-19500, and as follows. Electrical measurements (end-points) shall be in accordance with table I, subgroup 2 herein. Delta measurements shall be in accordance with table II herein.

4.4.3.1 Group C inspection, table VII of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
C6	1026	$I_O = 0.75 \text{ A}$ , $V_{RWN} = 45 \text{ V(pk)}$ , $T_A = +25^\circ\text{C}$ .
C7		Operational power cycling, see 4.5.6, $T_{C(Low)} = +40^\circ\text{C}$ , $+0$ , $-15^\circ\text{C}$ ; $T_{C(High)} = +115^\circ\text{C} +5$ , $-0^\circ\text{C}$ , 5,000 cycles, $n = 22$ , $c = 0$ .

4.5 Methods of inspection. Methods of inspection shall be as specified in the appropriate tables as follows.

\* 4.5.1 Pulse measurements. Conditions for pulse measurements shall be as specified in section 4 of MIL-STD-750.

4.5.2 Peak reverse energy test. The peak reverse energy test is to be performed as shown on figure 4 or equivalent. The diode under test must be capable of absorbing the reverse energy, as defined, and meet the electrical requirements of table I, subgroup 4 herein.

4.5.3 Thermal resistance. Thermal resistance shall be measured in accordance with method 4081 of MIL-STD-750. The case reference temperature shall be held to equilibrium within the range of  $+20^\circ\text{C}$  to  $+70^\circ\text{C}$  during the power application, and shall be measured at the hottest part of the case. The following measurements shall apply:  $I_{F1} = 1 \text{ A}$ , at 97 percent minimum duty factor;  $I_{F2} = 10 \text{ mA dc}$ .

\* 4.5.4 Reverse current at peak reverse voltage, alternate test. The reverse current at peak reverse voltage test may be satisfied by performing the reverse energy test of 4.5.2 and measuring breakdown voltage to ensure  $V_{(BR)} \geq 54 \text{ V (pk)}$  with  $I_{RM} = 2.0 \text{ A (pk)}$ . See figure 4.

\* 4.5.5 Scope display evaluation. Scope display evaluation shall be sharp and stable in accordance with method 4023 of MIL-STD-750. Scope display evaluation may be performed on ATE (automatic test equipment) for screening only with the approval of the qualifying activity. Scope display evaluation in group A shall be performed on an oscilloscope. One hundred percent scope test is required in the event of a group A failure, however group A resubmission criteria applies.

4.5.6 Operational power cycling (qualification only). One complete cycle for this test shall consist of the following two steps: Step 1, heat the case to the  $T_{c(high)}$  specified, by passing forward current through the diode under test. The reverse voltage shall be only enough to permit the reverse current to flow, and should be a maximum of 5 volts. Step 2, remove the applied current and allow the case temperature to cool to the  $T_{c(Low)}$  specified. Forward current shall be chosen to achieve the  $T_{c(high)}$  condition in  $75 \pm 50$  seconds. The cycling must be continuous until the required number of cycles has been completed. It is permissible to force cool the device during step 2.

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\* TABLE I. Group A inspection.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical inspection	2071					
<u>Subgroup 2</u>		<u>2/</u>				
Forward voltage	4011	$I_{FM} = 4.0 \text{ A(pk)}$ , pulsed (see 4.5.1)	$V_{FM2}$	0.68		V
	4011	$I_{FM} = 2.0 \text{ A(pk)}$ , pulsed (see 4.5.1)	$V_{FM3}$	0.56		V
	4011	$I_{FM} = 1.0 \text{ A(pk)}$ , pulsed (see 4.5.1)	$V_{FM4}$	0.48		V
	4011	$I_{FM} = 8.0 \text{ A(pk)}$ , pulsed (see 4.5.1)	$V_{FM1}$	0.92		V
Reverse current leakage	4016	$V_{RM} = 45 \text{ V(pk)}$ , pulsed method, (see 4.5.1)	$I_{RM1}$	2.0		mA
<u>Subgroup 3</u>		<u>2/</u>				
High temperature operation		$T_A = +125^\circ\text{C}$				
Reverse current leakage	4016	$V_{RM} = 45 \text{ V(pk)}$ , pulsed method, (see 4.5.1)	$I_{RM2}$	20		mA
High temperature operation		$T_A = +175^\circ\text{C}$				
Reverse current leakage	4016	$V_{RM} = 45 \text{ V(pk)}$ , pulsed method, (see 4.5.1)	$I_{RM3}$	200		mA
Low temperature operation		$T_A = -55^\circ\text{C}$				
Reverse current leakage	4016	$V_{RM} = 45 \text{ V(pk)}$ , pulsed method, (see 4.5.1)	$I_{RM4}$	20		mA
Forward voltage	4011	$I_{FM} = 2.0 \text{ A(pk)}$ , pulsed (see 4.5.1)	$V_{FM5}$	0.63		V
<u>Subgroup 4</u>						
Reverse current leakage at peak reverse voltage	4016	Pulsed method (see 4.5.1) $V_{RSM} = 54 \text{ V(pk)}$ , (alternate test, see 4.5.4) <u>2/</u>	$I_{RM5}$	2.0		A
Capacitance	4001	$V_R = 5 \text{ V}$ , $.01 \leq f \leq 1 \text{ MHz}$ $V_{SIG} = 15 \text{ mV(p-p)}$	$C_T$	450		pF
Scope display evaluation	4023	Sharp and stable (see 4.5.5) $n = 116$ , $c = 0$				
<u>Subgroup 5</u>						
Surge current	4066	$I_{FSM} = 80 \text{ A(pk)}$ , $V_{RM} = 45 \text{ V(pk)}$ , $I_O = 0.75 \text{ A}$ 10 surges of 8.3 ms each at 1 minute intervals, $T_A = +25^\circ\text{C}$				
Electrical measurements		See table I, subgroup 2 herein				

1/ See MIL-PRF-19500 for sampling plan.

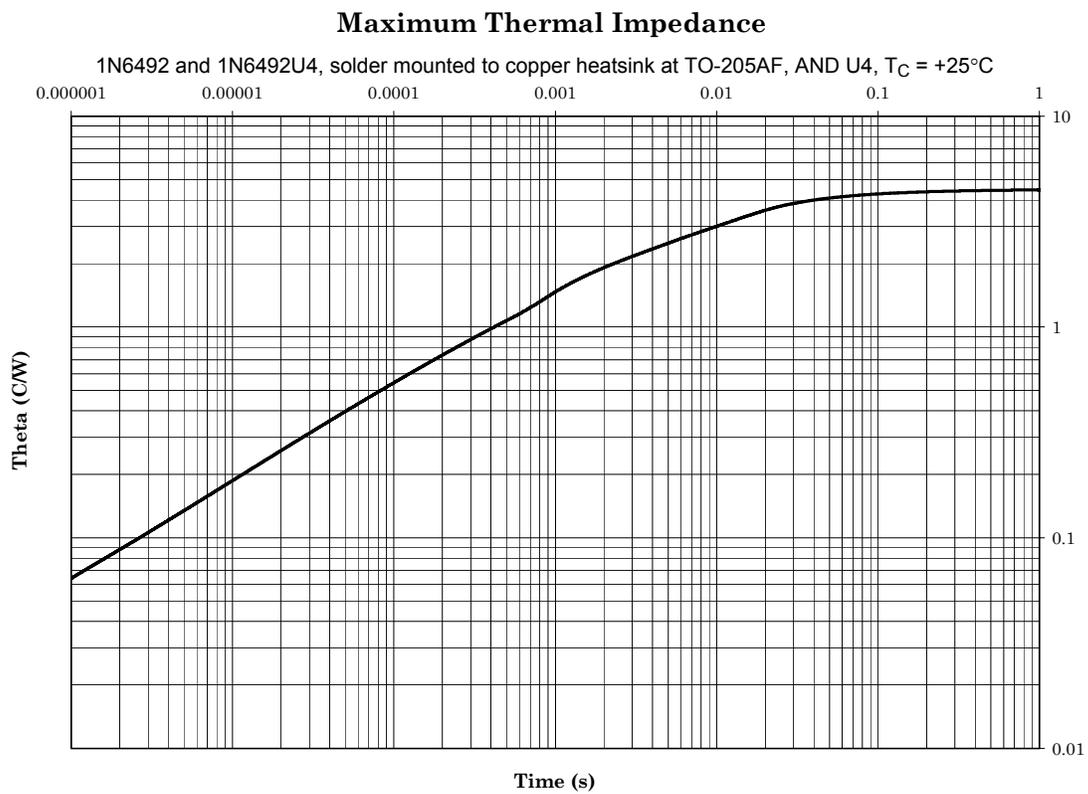
2/ Measurement point is on the lead .2 inch (5.08 mm) below the seating plane of the case.

\* TABLE II. Groups B and C delta tests. 1/ 2/

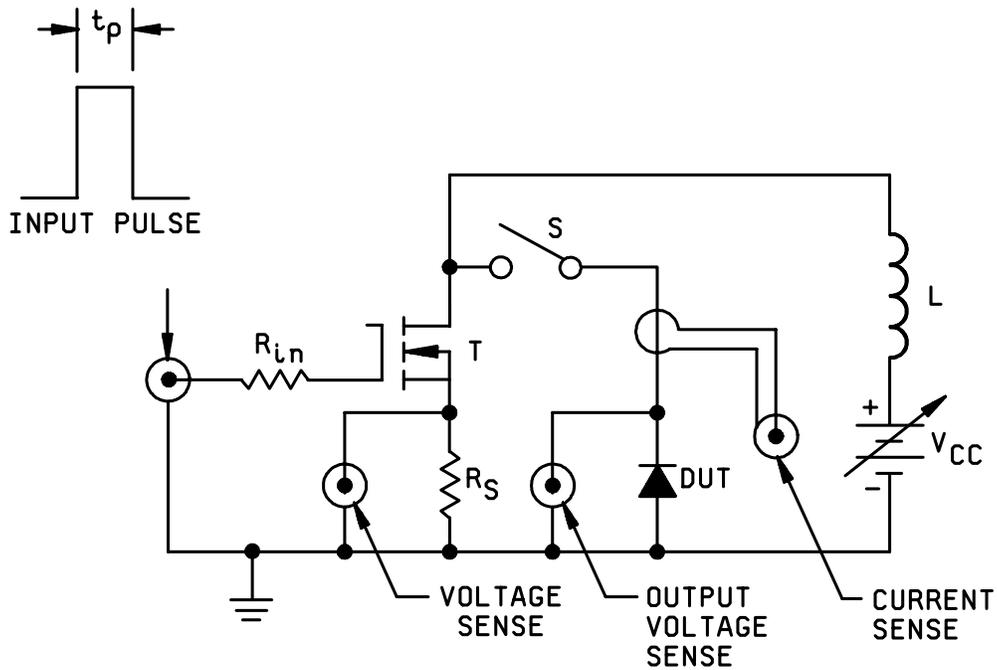
Step	Inspection	MIL-STD-750		Symbol	Limits		Unit
		Method	Conditions		Min	Max	
1.	Forward voltage	4011	$I_{FM} = 4 \text{ A(pk)}$ pulsed (see 4.5.1)	$\Delta V_{FM2}$	$\pm 50 \text{ mV}$ change from previous value		V
2	Reverse current	4016	$V_{RM} = 45 \text{ V(pk)}$ pulsed (see 4.5.1)	$\Delta I_{RM1}$	+500 $\mu\text{A}$ dc or +100 percent of initial value, whichever is greater		mV

1/ The delta measurements for table VIa (JANS) of MIL-PRF-19500 are as follows: Subgroups 4 and 5, see table II herein, steps 1 and 2.

2/ The delta measurements for table VII of MIL-PRF-19500 are as follows: Subgroup 6, see table II herein, steps 1 and 2.



\* FIGURE 3. Thermal impedance graph ( $R_{\theta JC}$ ) for 1N6492 and 1N6492U4 (TO-205AF and U4).



$V_G = 10$  Volts  
 $R_G = 50 \Omega$   
 $PW = 30 \mu s$   
 Duty cycle  $\leq 1$  percent

$R_{in} = 5.0 \Omega$ ohms, 1 W  
 $R_S = 0-1 \Omega$ , 1 W  
 $L = 260 \mu H$   
 $T =$  IRF130/2N6756 or equivalent

- Procedure:
1. With S open, adjust pulse width to test current of 2 A across  $R_S$ .
  2. Close S. Verify test current with current sense.
  3. Read peak output voltage (see 4.5.4).

\* FIGURE 4. Peak reverse energy test circuit.

## 5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD personnel, these personnel need to contact the responsible packaging activity to ascertain requisite packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activity within the Military Department or Defense Agency, or within the Military Department's System Command. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

## 6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory.)

6.1 Intended use. The notes specified in MIL-PRF-19500 are applicable to this specification.

6.2 Acquisition requirements. Acquisition documents must specify the following:

- a. Title, number, and date of this specification.
- b. Issue of DoDISS to be cited in the solicitation, and if required, the specific issue of individual documents referenced (see 2.2.1).
- c. Packaging requirements (see 5.1).
- d. Product assurance level and type designator.
- e. Lead finish (see 3.4.1).

6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers' List (QML) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from Defense Supply Center, Columbus, ATTN: DSCC/VQE, P.O. Box 3990, Columbus, OH 43216-5000.

6.4 Changes from previous issue. The margins of this specification are marked with asterisks to indicate where changes from the previous issue were made. This was done as a convenience only and the Government assumes no liability whatsoever for any inaccuracies in these notations. Bidders and contractors are cautioned to evaluate the requirements of this document based on the entire content irrespective of the marginal notations and relationship to the last previous issue.

### Custodians:

Army - CR  
Navy - EC  
Air Force - 11  
DLA - CC

### Preparing activity:

DLA - CC  
  
(Project 5961-2601)

### Review activities:

Army - AR, MI  
Navy - MC, SH  
Air Force - 19, 71, 99

**STANDARDIZATION DOCUMENT IMPROVEMENT PROPOSAL**

**INSTRUCTIONS**

1. The preparing activity must complete blocks 1, 2, 3, and 8. In block 1, both the document number and revision letter should be given.
2. The submitter of this form must complete blocks 4, 5, 6, and 7.
3. The preparing activity must provide a reply within 30 days from receipt of the form.

NOTE: This form may not be used to request copies of documents, nor to request waivers, or clarification of requirements on current contracts. Comments submitted on this form do not constitute or imply authorization to waive any portion of the referenced document(s) or to amend contractual requirements.

<b>I RECOMMEND A CHANGE:</b>	1. DOCUMENT NUMBER MIL-PRF-19500/567C	2. DOCUMENT DATE 12 September 2003
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3. **DOCUMENT TITLE** SEMICONDUCTOR DEVICE, DIODE, SILICON, SCHOTTKY BARRIER, FAST RECOVERY, TYPE 1N6492, 1N6492U4, JAN, JANTX, JANTXV, AND JANS

4. **NATURE OF CHANGE** (Identify paragraph number and include proposed rewrite, if possible. Attach extra sheets as needed.)

5. **REASON FOR RECOMMENDATION**

6. **SUBMITTER**

a. NAME (Last, First, Middle initial)	b. ORGANIZATION		
c. ADDRESS (Include Zip Code)	d. TELEPHONE (Include Area Code)	7. DATE SUBMITTED	
	COMMERCIAL DSN FAX EMAIL		

8. **PREPARING ACTIVITY**

a. Point of Contact Alan Barone	b. TELEPHONE		
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c. ADDRESS Defense Supply Center Columbus, ATTN: DSCC-VAC P.O. Box 3990 Columbus, OH 43216-5000	IF YOU DO NOT RECEIVE A REPLY WITHIN 45 DAYS, CONTACT: Defense Standardization Program Office (DLSC-LM) 8725 John J. Kingman, Suite 2533 Fort Belvoir, VA 22060-6221 Telephone (703) 767-6888 DSN 427-6888		